TV TRANSISTORS

TYPE	RF CHARACTERISTICS					I_{CMax} (A)	θ_{jc} (°C/W)	PACKAGE
	OUTPUT (W) power	Min. GAIN (dB)	VOLTAGE (V)	F (MHz)	IMD* (dB)			
TPV 366	1.5	17	25	BAND 3	— 60	0.75	8.0	SOE 280
TPV 394	5	15	28	BAND 3	— 58	4	2.5	SOE 280
TPV 364	10	10	25	BAND 3	— 55	9	2.0	SOE 380
TPV 385	14	14	28	BAND 3	— 55	10	1.5	JO 500
TPV 386	30	10	28	BAND 3	— 53	16	1	JO 500
TPV 590	0.250	14	20	BAND 4-5	— 60	0.4	30	SOE 200
TPV 591	0.500	13	20	BAND 4-5	— 60	0.8	16	SOE 200
TPV 597	1	11	20	BAND 4-5	— 60	1.4	9	SOE 280
TPV 598	4.0	7	25	BAND 4-5	— 60	2.5	5	SOE 280
TPV 599	7.5	7	20	BAND 4-5	— 60	4.5	2.5	MRA

* VISION - 8 dB, SOUND - 7 dB, SIDEBAND - 17 dB

CATV HYBRIDS

TYPE	P_{out} DIN 45004 B (dBmV)	GAIN (dB)	BAND-WIDTH (MHz)	NOISE FIGURE (dB)	SLOPE CABLE EQUIVALENT (dB)	V_{CC} (V)	OPERATING TEMPERATURE (°C)	PACKAGE
CA 2150/2250	63.5	17	40-300	7.5	+ 0.3/+ 1.0	24	— 20 to + 90	CA
CA 2152/2252	63.5	12	40-300	8.5	+ 1.0/+ 2.0	24	— 20 to + 90	CA
CA 2350A/2350B	63.5	22	40-300	6.5	+ 0.0/+ 1.0	24	— 20 to + 90	CA
CA 2650	63.0	33	40-300	7.0	+ 0.5/+ 1.5	24	— 20 to + 90	CA
CA 2750	64.0	38	40-300	7.5	+ 0.5/+ 1.5	24	— 20 to + 90	CA
CA 227X	65.0	12.5	40-300	7	+ 0.2/+ 0.7	24	— 20 to + 90	CA
CA 228X	65.0	17.5	40-300	7	+ 0.2/+ 0.7	24	— 20 to + 90	CA
CA 268X	64.5	34	40-300	6	+ 0.0/+ 1.95	24	— 20 to + 90	CA

MATV TRANSISTORS

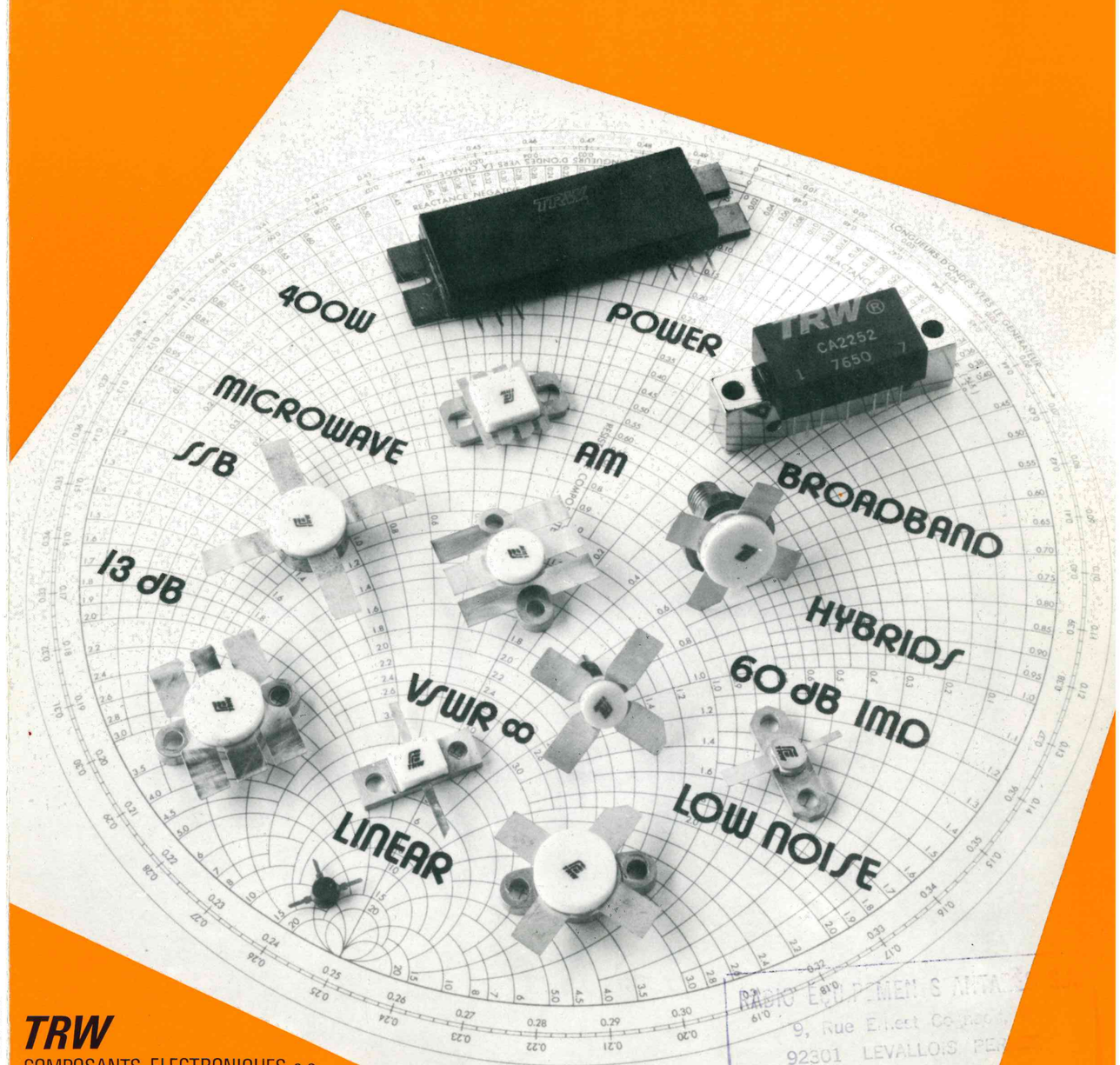
TYPE	RF CHARACTERISTICS (500 MHz)				V_{CEO} (V)	V_{CBO} (V)	PACKAGE
	OUTPUT CAPABILITY (mVolt)	GU MAX (500 MHz)	NF (dB)	FT (GHz)			
TP 393	300	15.5	2	3	14	25	T-PACK
TP 491	400	16.5	1.6	3.3	14	25	T-PACK
BFR 91	400	17.0	1.3	5.0	14	20	T-PACK
BFR 96	700	15.0	3.5	5.0	15	20	T-PACK
TP 3094	1000	13.5	4	2.6	25	30	TO-117
TPV 596	1500	17	—	2.5	24	45	SOE 280

LOW NOISE TRANSISTORS

TYPE	TECHNOLOGY	RF CHARACTERISTICS			
		F (GHz)	NOISE FIGURE (dB)	GAIN (dB)	OUTPUT POWER (dBm)
TPL 1200	Si Bipolar	2	3.6	7	18
TPL 2400	Si Bipolar	4	2.7	8	12
TPL 4800	GaAs FET	8	3	9	8.5

TRW® RF SEMICONDUCTORS

QUICK SELECTION GUIDE FROM 1 MHz UP TO 5 GHz



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UFI/Pessac

SSB TRANSISTORS

TYPE *	RF CHARACTERISTICS				V_{CEO}	V_{CBO}	$I_{CMax.}$	θjc	PACKAGE
	OUTPUT (W) power	Min. GAIN (dB)	VOLTAGE (V)	F (MHz)	(V)	(V)	(A)	(°C/W)	
PT 9795/A	15	15	13.5	28	20	50	4	3.0	380 SOE/F
PT 9796/A	30	15	13.5	28	20	50	8	2.5	380 SOE/F
PT 9797/A	50	15	13.5	28	20	50	12	2.0	380 SOE/F
PT 9784/A	75	15	13.5	28	20	50	15	1.4	380 SOE/F
PT 9785	100	13	13.5	28	20	50	25	0.9	380 SOE/F
PT 9787/A	8	14	28	28	40	70	2	7.0	380 SOE/F
PT 9788/A	20	14	28	28	40	70	4	2.5	380 SOE/F
PT 9783/A	50	14	28	28	40	70	10	1.0	380 SOE/F
PT 9780/A	100	14	28	28	40	70	20	0.5	500 SOE/F
LOT 1000	200	14	50	30	110	110	25	0.42	LOT

* A SUFFIX DENOTE STUD PACKAGE.

FM TRANSISTORS

TYPE	RF CHARACTERISTICS			VSWR	$I_{C\,Max.}$	θjc	PACKAGE
	OUTPUT POWER at 108 MHz (W)	GAIN (dB)	Vcc (V)		(A)	(°C/W)	
TP 9380	75	10.3	28	4 : 1	10	1.5	500 SOE
TP 9381	100	7.4	28	∞	12	1.1	500 SOE
TP 9382	175	6.4	28	∞	20	0.7	500 SOE
TP 9383	150	9.2	28	4 : 1	16	1.0	500 SOE

MOBILE TRANSISTORS AND MODULES

TYPE	RF CHARACTERISTICS				V_{CEO}	V_{CBO}	$I_{CMax.}$	θjc	PACKAGE
	OUTPUT (W) power	Min. GAIN (dB)	VOLTAGE (V)	F (MHz)	(V)	(V)	(A)	(°C/W)	
TP 2312	3	15.7	12.5	88	16	35	0.7	25	TO-39 GE
TP 2320	20	11.2	12.5	88	18	40	6	3.5	380 SOE
TP 2180	80	7.0	12.5	88	18	40	16	1.25	J-ZERO-C
TP 2314	4	12.0	12.5	175	16	36	1	20	TO-39 GE
PT 8828	9	11.1	12.5	175	16	36	3.4	3.5	380 SOE
TP 2320	17	8.2	12.5	175	18	40	6	3.5	380 SOE
TP 2303	30	6.0	12.5	175	18	40	7	2.5	380 SOE
TP 2304	40	5.2	12.5	175	18	40	8	2.2	380 SOE
JO 4070	70	5.9	12.5	175	18	40	12	1.25	J-ZERO-C
TP 250	0.01	10.0	7.5	470	18	35	200		T-PACK
TP 251	0.175	12.4	7.5	470	18	40	0.2	175	200 STUDLESS
TP 252	1.50	10.0	7.5	470	14	30	1	10	280 SOE
PT 8809	2	10.0	12.5	470	16	36	0.75	10	280 SOE
PT 8810	5	8.5	12.5	470	16	36	1.7	5	280 SOE
PT 8811	10	6.0	12.5	470	16	36	3.4	3.5	280 SOE
JO 3055	55	4.4	12.5	470	17	38	10	1.75	J-ZERO-C
ML 20	20	21.2	12.5	68-88	50 Ω Impedance		40 % Efficiency		MVM
MV 20	20	20.0	12.5	140-175	50 Ω Impedance		40 % Efficiency		MVM
MX 15	15	19.0	12.5	400-470	50 Ω Impedance		35 % Efficiency		MXM

VHF/UHF TRANSISTORS

TYPE	RF CHARACTERISTICS				V_{CEO}	V_{CBO}	$I_{CMax.}$	θjc	PACKAGE
	OUTPUT (W) power	Min. GAIN (dB)	VOLTAGE (V)	F (MHz)	(V)	(V)	(A)	(C°/W)	
PT 9730	4	13	28	175	35	60	1	17.5	380 SOE
PT 9732	8	12	28	175	35	60	1.25	8.8	380 SOE
PT 9734	15	11.7	28	175	35	60	2.5	5.8	380 SOE
PT 9731	25	10	28	175	35	60	4	3.9	380 SOE
PT 9733	50	8	28	175	35	60	8	2.1	380 SOE
JO 1006	100	7	28	100-180	35	60	12	0.88	J-ZERO-C
TPM 401	1	13	20	100-400	24	45	0.7	20	280 SOE
TPM 405	5	16	24	100-400	24	45	1.4	9.5	280 SOE
TPM 425	25	9	24	100-400	25	45	2	5	280 SOE
JO 2015 A	50	10	28	225-400	30	65	10	1.25	J-ZERO-C

RF HYBRIDS

TYPE	RF CHARACTERISTICS					I_{CMax}	OPERATING TEMPERATURE (°C)	PACKAGE
	OUTPUT POWER 1 dB COMPRES-SION (mW)	BROADBAND GAIN (dB)	VOLTAGE (V)	BANDWIDTH (MHz)	Zin et Zout (Ω)	mA		
CA 2800	800	17	24	10-400	50	220	— 20/+ 90	CA
CA 2820	400	30	24	1-520	50	360	— 40/+ 100	CA
CA 2832	2 W	35	28	1-200	50	470	— 40/+ 90	CA
CA 2870	400	34	24	20-400	50	330	— 40/+ 100	CA
CA 2876	100	22	19	40-100	75	80	— 40/+ 100	CA

MICROWAVE TRANSISTORS

TYPE	RF CHARACTERISTICS				V_{CEO}	V_{CBO}	OPERATING MODE	θjc (°C/W)	PACKAGE
	HIGHEST POWER DEVICE (W)	Min. GAIN (dB)	VOLTAGE (V)	F (GHz)	(V)	(V)			
TRW 52600 SERIES	6	10	20	1	24	45	LINEAR	6	HLP-8
TRW 53600 SERIES	1.6	8	20	2	24	45	LINEAR	17	HLP-8
TRW 54600 SERIES	0.5	5	20	4	24	45	LINEAR	40	HLP-8
TRW 62600 SERIES	2	—	20	2.5	22	45	OSCIL-	8.5	HLP-8
TRW 63600 SERIES	0.85	—	20	3	22	45	LATOR	17	HLP-8
TRW 64600 SERIES	0.65	—	20	4	22	45		40	HLP-8
TRW 2000 SERIES	20	5.2	28	2	28	45	CW	3	HLP-11/8
TRW 2300 SERIES	7	8.4	20	2.3	24	42	CW	8.5	HLP-8
TRW 3000 SERIES	5	5	28	3	28	45	CW	8.5	HLP-8
MRA 0610 SERIES	40	7	28	0.6-1.0	28	45	CW	2.5	MRA
MRA 1014 SERIES	35	7	28	1.0-1.4	28	45	CW	2	MRA
MRA 1417 SERIES	25	7	28	1.4-1.7	28	45	CW	2.5	MRA
MRA 1720 SERIES	20	6	28	1.7-2.0	28	45	CW	2.5	MRA
MRAL 2023 SERIES	12	7	22	2.0-2.3	24	42	CW	4.5	MRA
MRAL 2327 SERIES	12	7	22	2.3-2.7	24	42	CW	4.5	MRA
MRP 0912 SERIES	250	6.5	50	0.9-1.2	50	65	PULSE	—	MRP
MRP 1214 SERIES	85	6.5	28	1.2-1.4	28	45	PULSE	—	MRP